Silicon Diode

CBAS17

0.7V / 250mA

DATASHEET

OEM – Central Semiconductor Corp.

Source: Central Databook 2004

CBAS17

SURFACE MOUNT
LOW VOLTAGE
SILICON STABISTOR

SOT-23 CASE

Central™
Semiconductor Corp.

DESCRIPTION:
The CENTRAL SEMICONDUCTOR CBAS17 type is a planar epitaxial silicon switching diode, designed for low voltage stabilizing applications.

MARKING CODE: A91

MAXIMUM RATINGS: (T_A=25°C unless otherwise noted)

	SYMBOL		UNITS
Peak Repetitive Forward Current	I_{FRM}	250	mA
Power Dissipation	P_D	350	mW
Operating and Storage Junction Temperature	T_J,T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
V_F	I_F=0.1mA	.580	.665	.680	V
V_F	I_F=1.0mA	.665	.745	.760	V
V_F	I_F=5.0mA	.725	.805	.820	V
V_F	I_F=10mA	.750	.825	.840	V
V_F	I_F=100mA	.870	.920	.960	V
I_R	V_R=4.0V			5.0	μA
C_T	V_R=0, f=1MHz			140	pF

For Typical Electrical Characteristic Data for this device, please see Process CPD63 on page 882.

R5 (6- August 2003)

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CBAS17

SURFACE MOUNT
LOW VOLTAGE
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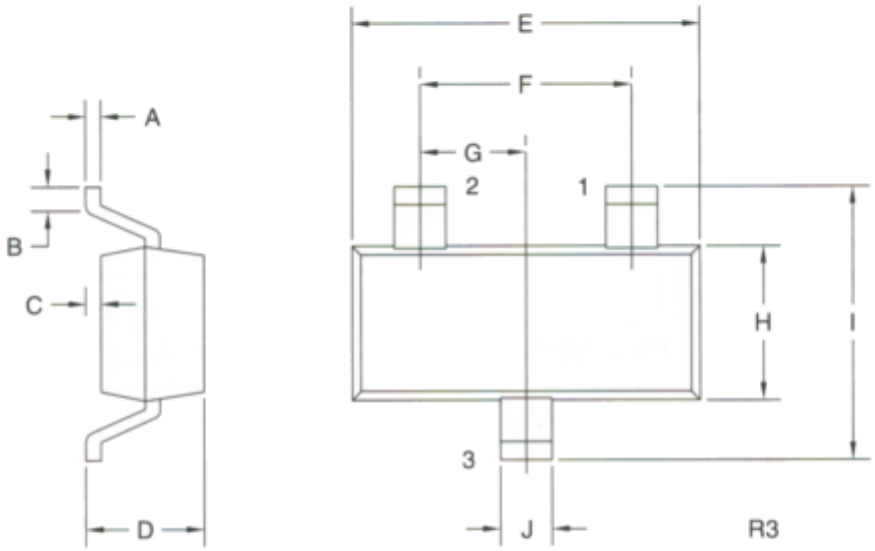
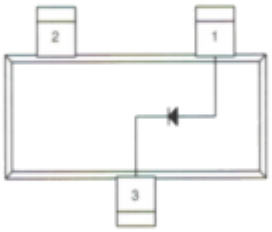
SOT-23 CASE - MECHANICAL OUTLINE





LEAD CODE:
1) ANODE
2) NO CONNECTION
3) CATHODE

MARKING CODE: A91

DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)

R5 (6- August 2003)